



## Future Normal in Semiconductor

2025-02-14(금), 15:10-17:10

좌장: 추후업데이트 예정

### D. Thin Film Process Technology 분과

#### [FC3-D] Atomic Layer Deposition – III

<p>FC3-D-1 15:10-15:25</p>	<p><b>Area-selective Atomic Layer Deposition of Ruthenium Thin Films via Atmospheric Pressure Plasma Technology</b> Dahui Jeon<sup>1,2</sup> and In-Hwan Baek<sup>1,2</sup> <sup>1</sup>Department of Chemical Engineering, Inha University, <sup>2</sup>Program in Semiconductor Convergence, Inha University</p>
<p>FC3-D-2 15:25-15:40</p>	<p><b>Inherent Area-Selective Deposition of Low-resistivity Molybdenum Carbide Films by Thermal Atomic Layer Deposition</b> Ji Sang Ahn and Jeong Hwan Han Department of Materials Science and Engineering, Seoul National University of Science and Technology</p>
<p>FC3-D-3 15:40-15:55</p>	<p><b>Theoretical Development of Area-Selective Atomic Layer Deposition Process of Ruthenium via Reduction of Interfacial Oxidation</b> Iaen Cho<sup>1,2</sup>, Eun-Hyoung Cho<sup>3</sup>, Dabin Kong<sup>4</sup>, Youngchul Leem<sup>3</sup>, Young Min Lee<sup>3</sup>, Miso Kim<sup>1</sup>, Chi Thang Nguyen<sup>4</sup>, Jeong Yub Lee<sup>3</sup>, Han-Bo-Ram Lee<sup>4</sup>, and Bonggeun Shong<sup>1</sup> <sup>1</sup>Hongik University, <sup>2</sup>Yonsei University, <sup>3</sup>Samsung Advanced Institute of Technology, <sup>4</sup>Incheon National University</p>
<p>FC3-D-4 15:55-16:10</p>	<p><b>In-Situ Hydrogen Gas Annealing in ALD Reactor for Improved Quality of Cobalt Thin Film</b> Jaeseong Pyo, Giryun Hong, Jongseo Park, Bohyeon Kang, Jehyun An, Beomjoo Ham, Sung-Min Ahn, and Rock-Hyun Baek Department of Electrical Engineering, POSTECH</p>
<p>FC3-D-5 16:10-16:25</p>	<p><b>Development of Atomic Layer Etching of ZrO<sub>2</sub> Thin Films Using NF<sub>3</sub> Plasma and TiCl<sub>4</sub></b> Haram Yang<sup>1</sup>, Hyeongjun Kim<sup>2</sup>, and Woongkyu Lee<sup>1,2</sup> <sup>1</sup>Department of Materials Science and Engineering, Soongsil University, <sup>2</sup>Department of Green Chemistry and Materials Engineering, Soongsil University</p>
<p>FC3-D-6 16:25-16:40</p>	<p><b>Growth Characteristics of ZrO<sub>2</sub>, HfO<sub>2</sub>, and In<sub>2</sub>O<sub>3</sub> Deposited by Liquid Injection Atomic Layer Deposition</b> Soon-Kyeong Park<sup>1</sup>, JunHee Cha<sup>2</sup>, and Il-Kwon Oh<sup>1,2</sup> <sup>1</sup>Department of Intelligence Semiconductor Engineering, Ajou University,</p>



# 제 32회 한국반도체학술대회

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	<sup>2</sup> Department of Electrical and Computer Engineering, Ajou University
<b>FC3-D-7</b> <b>16:40-16:55</b>	<b>Thermal Atomic Layer Deposition of AlN Films Using Tris(dimethylamido)aluminum and Ammonia</b> Okhyeon Kim, Yerim Choi, Jian Heo, Changgyu Kim, Hye-Lee Kim, and Won-Jun Lee Department of Nanotechnology and Advanced Materials Advanced Materials Engineering, Sejong University
<b>FC3-D-8</b> <b>16:55-17:10</b>	<b>High Temperature TiN Atomic Layer Deposition using N-containing Reactants</b> Hyewon Park, Yoonseo Choi, and Han-Bo-Ram Lee Department of Materials Science and Engineering, Incheon National University